

### **Amendments to the Claims**

This listing of claims will replace all prior versions, and listings of claims in the application:

#### **Listing of Claims:**

Claim 1 (Currently Amended): A semiconductor device comprising:

- a substrate which has a main surface;
- an alignment mark which is formed on the main surface and which has a pattern, wherein the pattern in a plane view has a shape that is obtained by eliminating corners from a polygon; and
- an oxidation prevention cover film on the alignment ~~[[mask]]~~ mark and formed as having the pattern.

Claim 2 (Original): The semiconductor device as claimed in claim 1, wherein the polygon is a rectangle.

Claim 3 (Previously Presented): The semiconductor device as claimed in claim 1, wherein a width of the pattern of the alignment mark ranges from 0.6  $\mu\text{m}$  to 0.8  $\mu\text{m}$ .

Claim 4 (Previously Presented): The semiconductor device as claimed in claim 1, wherein the alignment mark is a metal film.

Claims 5-6 (Canceled)

Claim 7 (Previously Presented): The semiconductor device as claimed in claim 1, wherein a width of the pattern of the oxidation prevention cover film is 1  $\mu\text{m}$  to several  $\mu\text{m}$  wider at one side than a width of the pattern of the alignment mark.

Claim 8 (Previously Presented): The semiconductor device as claimed in claim 1, wherein the oxidation prevention cover film is formed of iridium-based metal.

Claim 9 (Previously Presented): A semiconductor device comprising:

- a substrate which has a main surface;
- an alignment mark which is formed on the main surface and which has first through fourth sub-patterns,
  - wherein the first and second sub-patterns are arranged so as to oppose each other, the third and fourth sub-patterns are arranged so as to oppose each other, and the first through fourth sub-patterns are separated from one another; and
- an oxidation prevention cover film on the alignment mark and formed as having the first through fourth sub-patterns.

Claim 10 (Previously Presented): The semiconductor device as claimed in claim 9, wherein a width of the sub-patterns of the alignment mark ranges from 0.6  $\mu\text{m}$  to 0.8

μm.

Claim 11 (Original): The semiconductor device as claimed in claim 9, wherein the alignment mark comprises a metal film.

Claims 12-13 (Canceled)

Claim 14 (Previously Presented): The semiconductor device as claimed in claim 9, wherein a width of the first through fourth sub-patterns of the oxidation prevention cover film is 1 μm to several μm wider at one side than a width of the first through fourth sub-patterns of the alignment mark.

Claim 15 (Previously Presented): The semiconductor device as claimed in claim 9, wherein the oxidation prevention cover film is formed of iridium-based metal.

Claim 16 (Previously Presented): A semiconductor device comprising:

- a substrate having a main surface;

- an alignment mark on the main surface of the substrate, wherein the alignment mark is strip-like and has the shape of a polygon without corners along a plane parallel to the main surface of the substrate; and

- an oxidation prevention cover film on the alignment mark, wherein the oxidation

prevention cover film is strip-like and has annular shape along another plane parallel to the main surface of the substrate.

Claim 17 (Previously Presented): The semiconductor device of claim 16, wherein the polygon is a rectangle.

Claim 18 (Previously Presented): The semiconductor device of claim 17, wherein the oxidation prevention cover film has rectangular annular shape.

Claim 19 (Previously Presented): The semiconductor device of claim 16, wherein the alignment mark has a width ranging from 0.6  $\mu\text{m}$  to 0.8  $\mu\text{m}$ .

Claim 20 (Previously Presented): The semiconductor device of claim 16, wherein a width of the oxidation prevention cover film is 1  $\mu\text{m}$  to several  $\mu\text{m}$  wider than a width of the alignment mark.

Claim 21 (Previously Presented): The semiconductor device of claim 16, wherein the alignment mark is a metal film.

Claim 22 (Previously Presented): The semiconductor device of claim 16, wherein the oxidation prevention cover film is an iridium based metal.